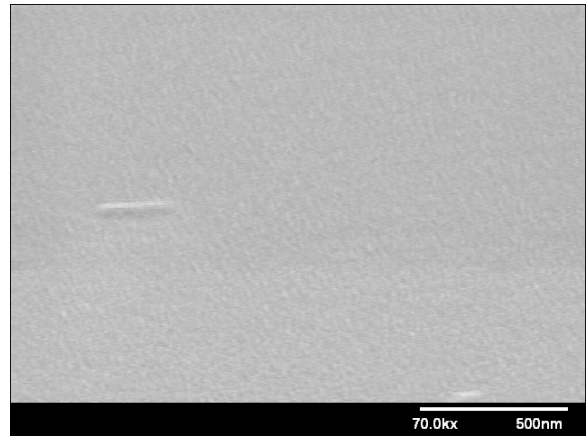
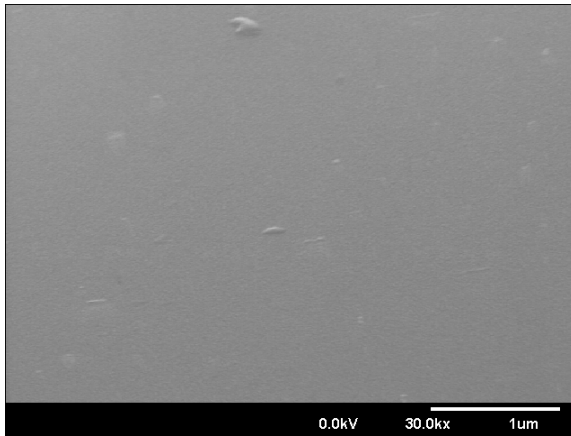
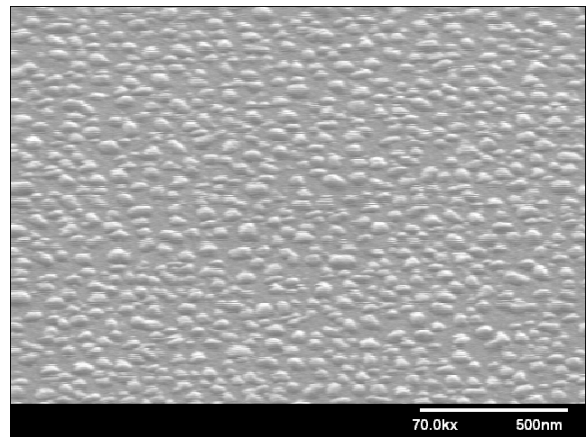
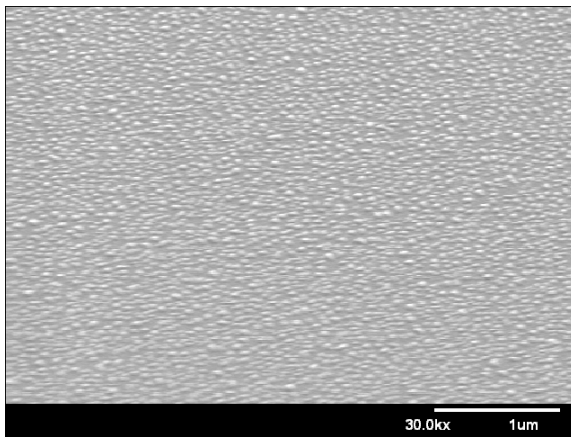


E1、600°C H₂:200 (Ni 1 nm)



E2、600°C H₂:200 (Ni 5 nm)



E3、600°C H₂:200 (Ni 7 nm)

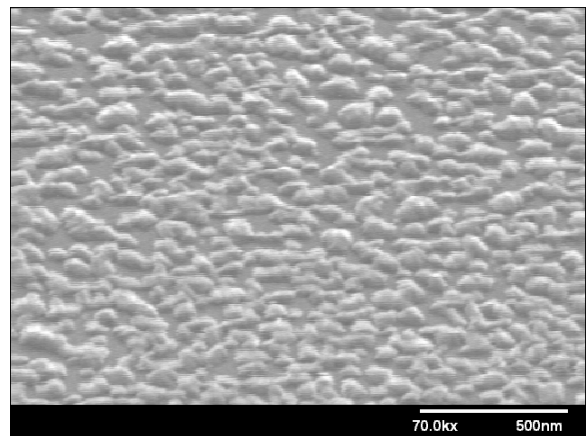
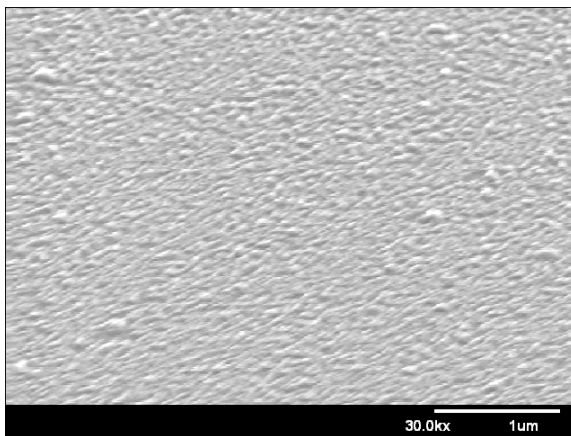
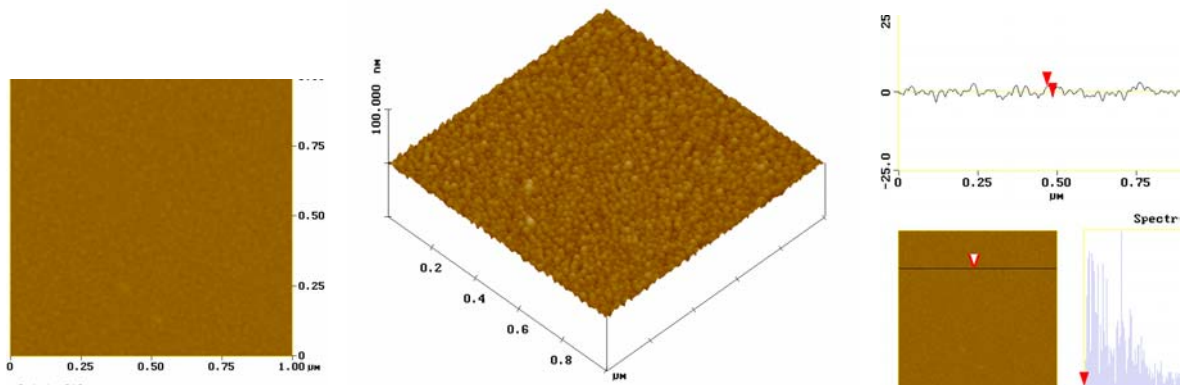
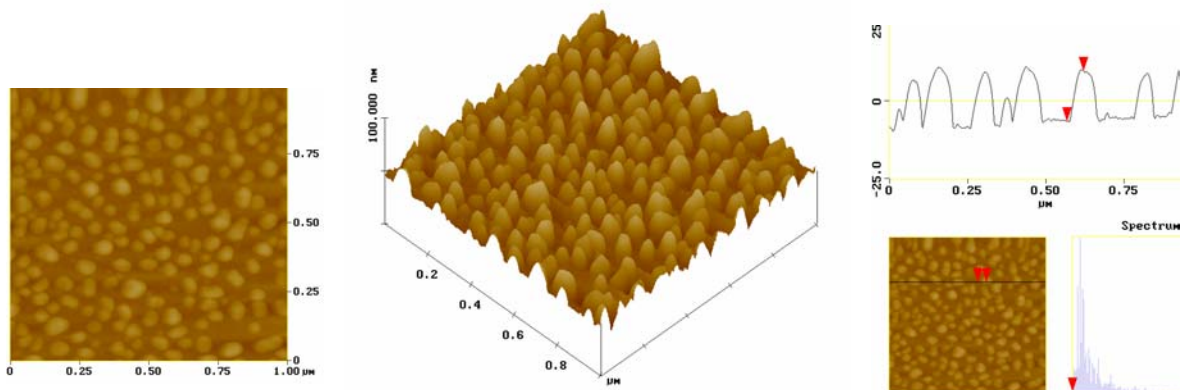


圖 4-14 製程 E 無緩衝層試件(1、2、3) SEM 圖面(30、70 kx)

E1、600°C H₂:200 (Ni 1 nm) ; Rms 1.037 nm



E2、600°C H₂:200 (Ni 5 nm) ; Rms 5.690 nm



E3、600°C H₂:200 (Ni 7 nm) ; Rms 9.175 nm

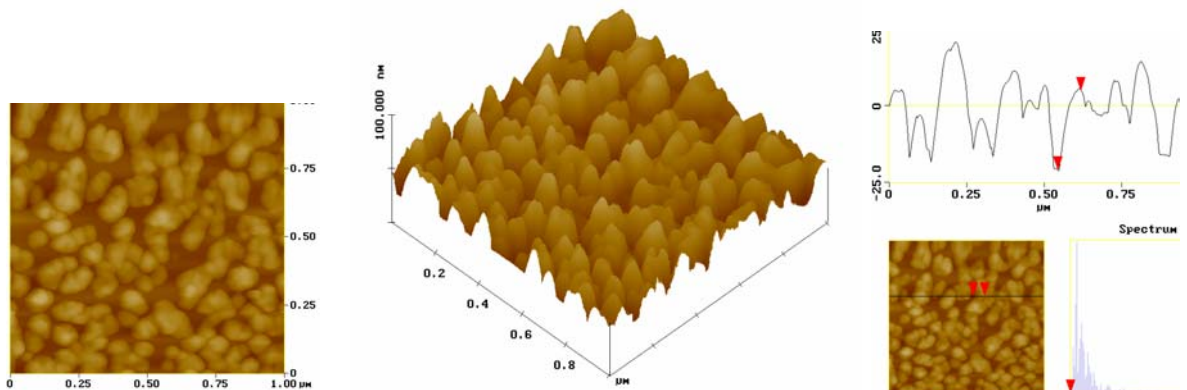
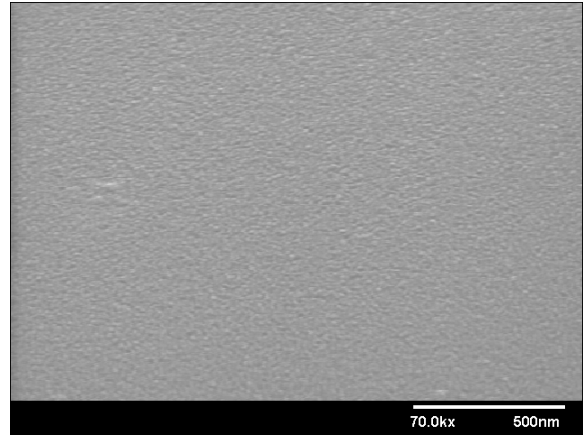
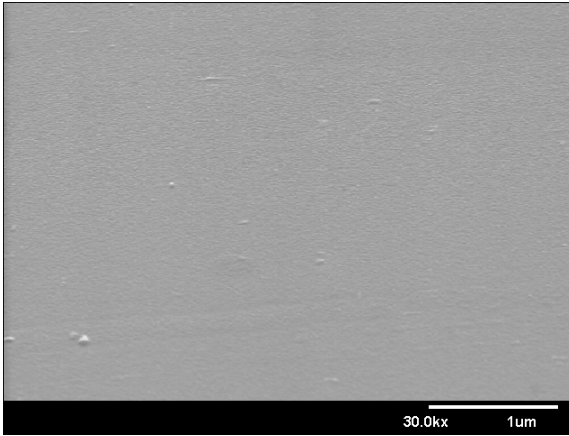
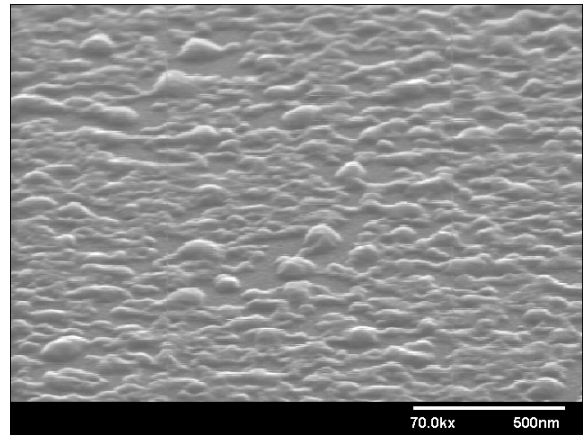
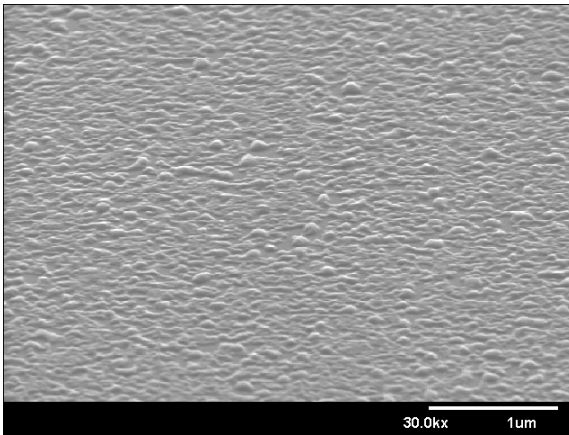


圖 4-15 製程 E 無緩衝層試件(1、2、3) AFM 圖面

A3、550°C H₂:100 (Ni 7 nm)



A4、550°C H₂:100 (Ni 7 / TiN 20 nm)



A5、550°C H₂:100 (Ni 7 / TaN 10 nm)

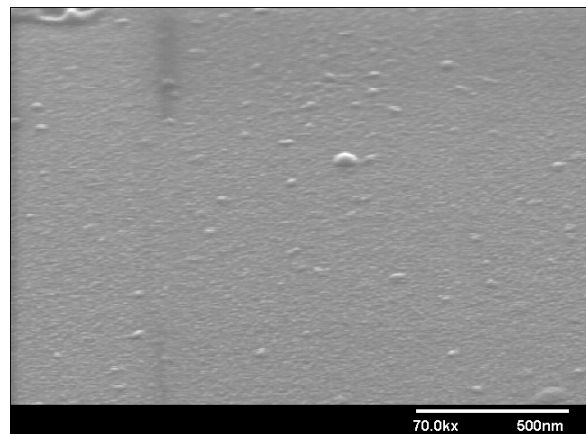
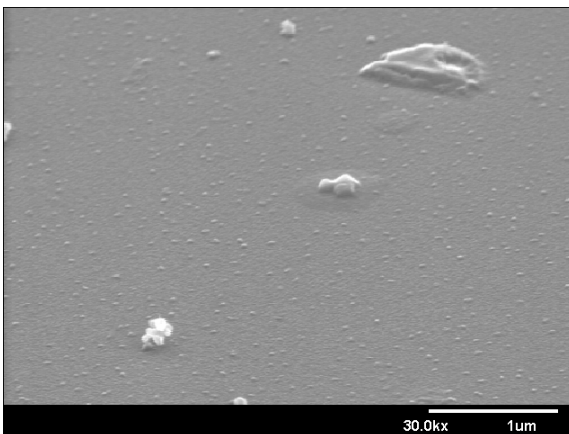
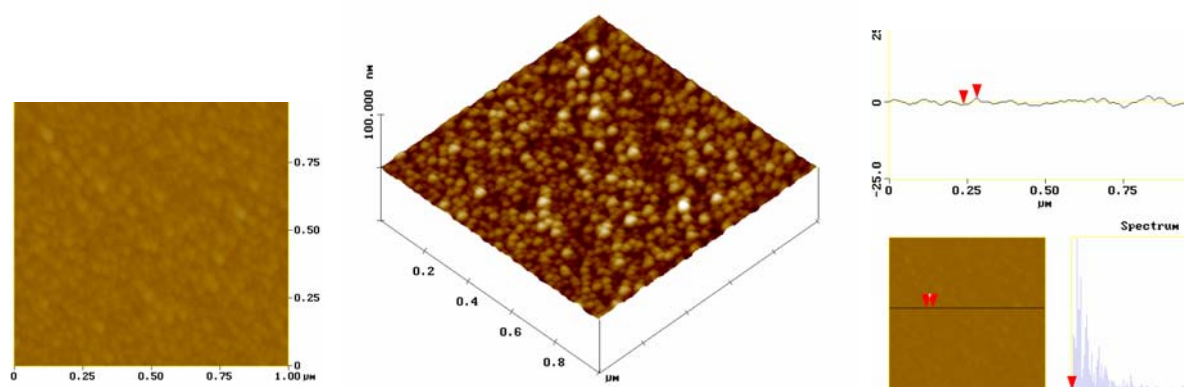
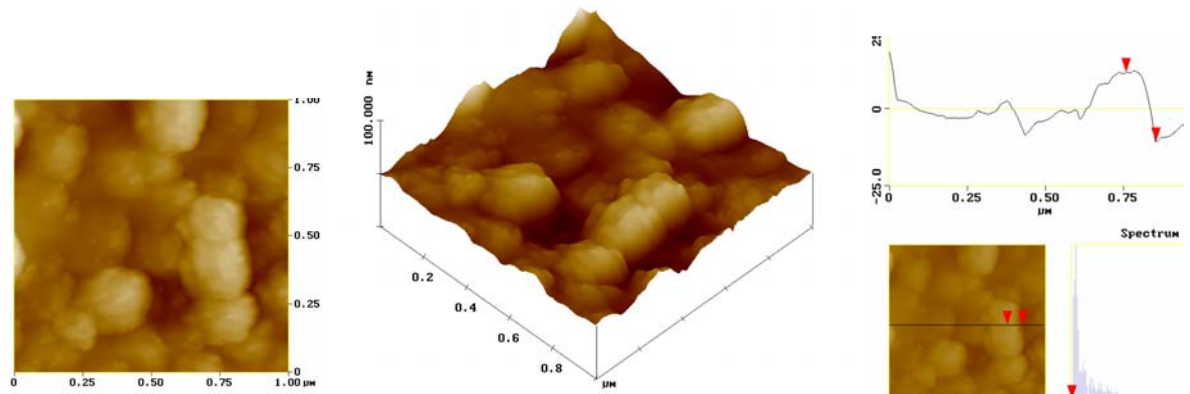


圖 4-16 製程 A 有緩衝層對照組試件(4、5) SEM 圖面(30、70 kx)

A3、550°C H₂:100 (Ni 7 nm) ; Rms 0.700 nm



A4、550°C H₂:100 (Ni 7 / TiN 20 nm) ; Rms 5.554 nm



A5、550°C H₂:100 Ni 7 / TaN 10 nm) ; Rms 4.700 nm

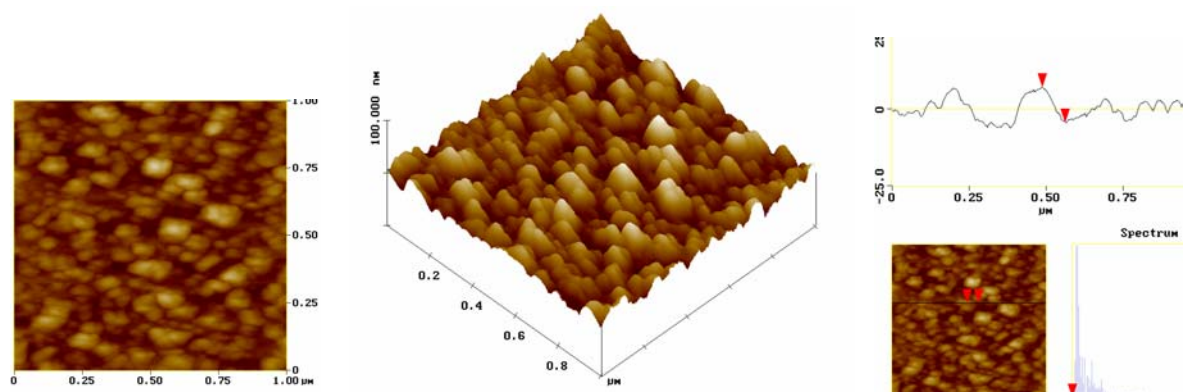


圖 4-17 製程 A 有緩衝層對照組試件(4、5)AFM 圖面